

AEC-Q100H Automotive Tier Qual Result					
Objective	IMX 31 AUTO MAPBGA Molding Compound G770SFL Qualification				
NXP Part #	MCIMX31Cxx/MCIMX31Lxx	Customer Name(s)	Varies	Results	Result
Part Name	IMX 31 AUTO	Pin(s)	Varies	Revision # & Date	See revision history
Technology Package	EN40LXX7 / CMOS00LP MAPBGA 473 19*19*1.12 P0.8	Design Engr.	NA	QUARTZ Tracking #	NA
Fab / Assembly / Final Test Site	SMC 12/NXP-ATTJ/NXP-ATTJ	Product Engr.	Cathy Chen	GAO Approval (for DIM/BOM results)	
Markets	IMB1E			Signature & Date	Jeanbo Chen
Die Size (in mm)		Prod. Pkg Engr.	Jeanbo Chen	NPI PROE Approval Signature & Date	Diogo Liu 14-Mar-2023
W/L	See C of DC in PPAP	NPI PROE	Diogo Liu	CAB Approval Signature & Date	2/20/2009
Part Operating Temp. Grade	AEC Q100 Grade3: -40°C to +85°C	Trace/Date/Code	N/A	Qualification Description: Upgrade molding compound from G770FL to G770SFL. The composition is same, but G770SFL has lower content of alpha filler. There is no changes of molding compound process/ recipe.	

TESTS HIGHLIGHTED IN YELLOW WILL BE PERFORMED FOR THIS STUDY
This testing is performed by NXP Reliability Lab (T-JN) unless otherwise noted in the Comments.

GROUP A - ACCELERATED ENVIRONMENTAL STRESS TESTS							
Stress Test	Reference	Test Conditions	End Point Requirements	Minimum Sample Size	# of Lots	Total Units including spares	Results Lot D-(R/R/SS) NA=Not Applicable
PC	JESD22-A113 J-STD-020	Preconditioning (PC): PC required for SMDs only. MSL 3 @ 260°C, +5/-0°C	TEST @ RH				pass
							Generic Data: Q243498.S32K144, MAPBGA 100 (CSM7, N57U): 0/462 Q218280.MCIMX31LCVMN4C, MAPBGA 473 (TSMC12, M91E): 0/231 Q221456.MPC8309, MAPBGA 489 (TSMC12, N83A): 0/94 Q224100.SPC5679KFF0MMS2, MAPBGA 473 (TSMC12, N83A): 0/154
HAST	JESD22-A110	Highly Accelerated Stress Test (HAST): PC before HAST for SMDs only. Required HAST = 10°C/260% for 24hrs Bias = Max Vdd	TEST @ RH	77	0	0	pass
UHST	JESD22-A118	Unbiased HAST (UHST): PC before UHST for SMDs only. Required UHST = 10°C/260%RH for 24hrs	TEST @ R	77	0	0	pass
TC	JESD22-A104 AEC Q100-Appendix 3	Temperature Cycle (TC): PC before TC (for SMDs only). Required TC = -55°C to 125°C for 500 cycles.	TEST @ H	77	0	0	pass
							Generic Data: Q218280.MCIMX31LCVMN4C, MAPBGA 473 (TSMC12, M91E): 0/231 Q221456.MPC8309, MAPBGA 489 (TSMC12, N83A): 0/94 Q224100.SPC5679KFF0MMS2, MAPBGA 473 (TSMC12, N83A): 0/154 Q221456.MPC8309, MAPBGA 489 (TSMC12, N83A): 0/94 Q224100.SPC5679KFF0MMS2, MAPBGA 473 (TSMC12, N83A): 0/154 Q221456.MPC8309, MAPBGA 489 (TSMC12, N83A): 0/94 Q224100.SPC5679KFF0MMS2, MAPBGA 473 (TSMC12, N83A): 0/154
HTSL	JESD22-A103	High Temperature Storage Life (HTSL): 150°C for 500 hrs	TEST @ RH	45	0	0	pass

TEST GROUP B - ACCELERATED LIFETIME SIMULATION TESTS							
Stress Test	Reference	Test Conditions	End Point Requirements	Minimum Sample Size	# of Lots	Total Units including spares	Results Lot D-(R/R/SS) NA=Not Applicable
HTOL	JESD22-A108	High Temperature Operating Life (HTOL): AEC Ta: Grade 3: 85°C for 1000 hours. Bias: 1.7V	TEST @ RH	77	0	0	pass
ELFR	AEC Q100-008	Early Life Failure Rate (ELFR): AEC Ta = 125°C for 48 hrs. Bias: 1.7V	TEST @ RH	800	0	0	pass
EDR	AEC Q100-005	WVW Endurance, Data Retention, and Operational Life (EDR): 150°C for 1000 hrs	TEST @ RCH	77	0	0	NA
		Devices incorporating NVM shall receive 1X NVM endurance preconditioning (W/E cycling). Test R, H, C after W/E cycling. Timed RD of 6hrs. MAX					Generic Data: Q190597.PPC8309VMA00C, MAPBGA 369 (TSMC12, N83A): 0/231 Q218280.MCIMX31LCVMN4C, MAPBGA 473 (TSMC12, M91E): 0/231 Q221456.MPC8309, MAPBGA 489 (TSMC12, N83A): 0/94 Q224100.SPC5679KFF0MMS2, MAPBGA 473 (TSMC12, N83A): 0/154

TEST GROUP C - PACKAGE ASSEMBLY INTEGRITY TESTS							
Stress Test	Reference	Test Conditions	End Point Requirements	Minimum Sample Size	# of Lots	Total Units including spares	Results Lot D-(R/R/SS) NA=Not Applicable
WBS	AEC Q100-001	Wire Bond shear (WBS)	Cpk = or > 1.67	30 bonds from minimum 5 units	0	0	NA
WBP	MIL8838-2011	Wire Bond Pull (WBP): Cond. C or D	Cpk = or > 1.67	30 bonds from minimum 5 units	0	0	NA
SD	JESD22-B102	Solderability (SD): 3hr (2 hr. for Au-plated leads) Steam age prior to test. If production burn-in is done, samples must also undergo burn-in prior to SD	>95% lead coverage of critical areas	15	0	0	NA
PD	JESD22-B100	Physical Dimensions(PD): PD per NXP drawing	Cpk = or > 1.67	10	0	0	Pass
DIM & BOM		Dimensional (DIM): GAO to verify PD results against valid NXP drawing. BOM Verification (BOM): GAO to verify test to ERF BOM is accurate.		10	0	0	DIM: pass BOM: approve
SBS	AEC-Q100-010	Solder Ball Shear (SBS): Performed on all solder ball mounted packages e.g. PBGA, Chip Scale, Micro Lead Frame (but NOT Flip Chip). Two reflow cycles at MSL reflow temperature before shear.	Cpk = or > 1.67	10 (5 balls from a min. of 10 devices)	0	0	NA
LI	JESD22-B105	Lead Integrity (LI): Not required for surface mount devices; Only required for through-hole devices.	No lead breakage or cracks	5 (10 leads from each of 5 parts)	0	0	NA

TEST GROUP E - ELECTRICAL VERIFICATION TESTS							
Stress Test	Reference	Test Conditions	End Point Requirements	Minimum Sample Size	# of Lots	Total Units including spares	Results Lot D-(R/R/SS) NA=Not Applicable
TEST	NXP 48A	Pre- and Post Functional / Parametrics (TEST): For AEC, test software shall meet requirements of AEC-Q100-007. Testing performed to the limits of device specification & temperature and limit value.	0 Fails	all	0	0	NA
HBM	AEC-Q100-007 JESD22-A114E Jan 2007	Electrostatic Discharge/ Human Body Model Classification (HBM): For AEC, see AEC-Q100-002 for classification levels.	TEST @ RH 2KV min.	3 units per Voltage level	0	0	NA
CDM	AEC-Q100-011	Electrostatic Discharge/ Charged Device Model Classification (CDM): Test @ 250/500 Volts For AEC, see AEC-Q100-011 for classification levels. Timed RD of 60hrs MAX.	TEST @ RH All pins >= 500V	3 units per Voltage level	0	0	NA
LU	JESD78 plus AEC-Q100-004 for AEC	Low-imp ESD: Test per JEDEC JESD78 with the AEC-Q100-004 requirements for AEC. Ta= Maximum operating temperature (Supply = Maximum operating voltage)	TEST @ RH	6	0	0	NA
ED	AEC-Q100-009 NXP 48A spec	Electrical Distribution (ED)	TEST @ RCH	30	0	0	NA
FG	For AEC, AEC-Q100-007	Fault Grading (FG)	FG shall be = or > 90% for qual units				
CHAR	For AEC, AEC-Q100	Characterization (CHAR): Only performed on new technologies and part families per AEC-Q100.		30	0	0	

Products Being Qualified					
Part Number (N)	Full Mask Set/Tech	Assembly Site	Pin Description	Mold Description	SPOXY Description
MCIMX31Cxx/MCIMX31Lxx	SMC12 M91E / H009H.X6	NXP-ATTJ	MAPBGA 473 19*19*1.8 P0.8	G770SFL	ABLEBOND 20250 20um PdCu
Die Qual Generic data					Solder ball composition: SNAG/Cu, 0.4um

Part Number (N)	Full Mask Set/Tech	Assembly Site	Pin Description	Mold Description	SPOXY Description	Wire Description	Solder Ball composition
Q243498	MCIMX31LCVMN4C	TSMC12 M91E / H009H.X6	NXP-ATTJ	MAPBGA 473 19*19*1.12 P0.8	G770SFL	ABLEBOND 20250 20um PdCu	SNAG/Cu, 0.4um
190597	PPC8309VMA00C	TSMC12 N83A / H009H.X7	NXP-ATTJ	MAPBGA 489 19*19*1.61 P0.8	G770SFL	ABLEBOND 20250 20um PdCu	SNAG, 0.4um

Part Number (N)	Full Mask Set/Tech	Assembly Site	Pin Description	Mold Description	SPOXY Description	Wire Description	Solder Ball composition
Q21456	SPC8309	TSMC12 N83A / H009H.X7	NXP-ATTJ	MAPBGA 489 19*19*1.61 P0.8	G770SFL	ABLEBOND 20250 20um PdCu	SNAG, 0.4um
Q243498	S32K144	CSM7 (N57U) / H009H.X6	NXP-ATTJ	MAPBGA 100 11*11*1.07 P1	G770SFL	ABLEBOND 20250 20um PdCu	SNAG, 0.4um
Q224100	SPC5679KFF0MMS2	ATAC (N57D) / H009H.X6	NXP-ATTJ	MAPBGA 473 19*19*1.8 P0.8	G770SFL	ABLEBOND 20250 20um Pd Cu	SNAG, 0.4um
MCIMX31DVN6D	TSMC12 M91E / H009H.X6	NXP-ATTJ	MAPBGA 473 19*19*1.8 P0.8	G770SFL	ABLEBOND 20250 20um Pd Cu	SNAG/Cu, 0.4um	

Revision	Date	Comments	Author
Rev. 1.0	14-Mar-23	Qual Report	Diogo Liu